



General Description

The ZM2301T combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Features

- high cell density Trench technology
- $R_{DS(ON)}$ to minimize conductive loss
- fast switching

Application

- Load Switch
- Display Screen Drive

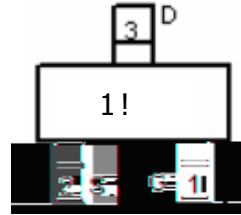
Product Summary



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Ordering Information:

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	A1H
	REEL TAPE
2	3000

Absolute Maximum Ratings $T_c = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	$I_{D@TC=25}$	-2.8	A
	$I_{D@TC=75}$	-2.1	A
	$I_{D@TC=100}$	-1.7	A
Pulsed Drain Current	I_{DM}	-10	A
Total Power Dissipation	P_D	10	W
Total Power Dissipation($T_A=25$)	$P_{D@TA=25}$	1.25	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	12.5	C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	100	C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	C

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(TH)}$	V				



Dimensions(SOT23)

Unit mm

